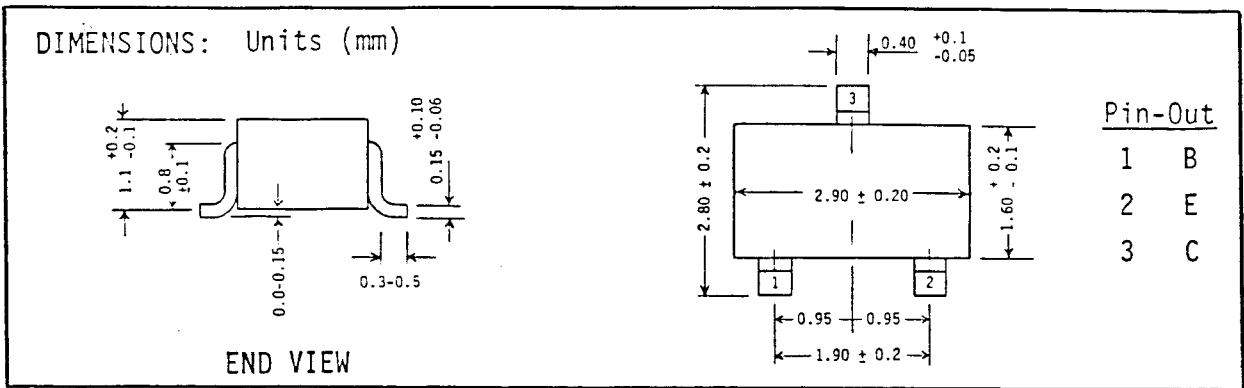
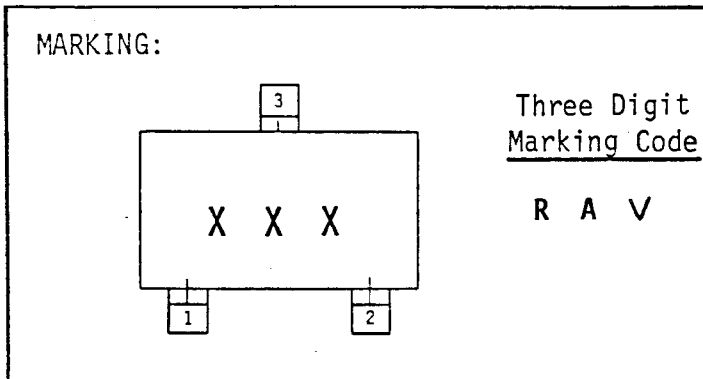


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SUBJECT SOT-23 TRANSISTOR, NPN, SILICON		
ABSOLUTE MAXIMUM RATINGS: (Ta = 25°C)		
Collector-Base Voltage	V _{CB0}	60 V
Collector-Emitter Voltage	V _{CE0}	60 V
Emitter-Base Voltage	V _{EB0}	6 V
Collector Current	I _C	200 mA
Power Dissipation-Free Air	P _D	200 mW
Power Dissipation-Ceramic Substrate	P _D	350 mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-55 to 150 °C
Solder Temperature (10 seconds)		260 °C



THE JAPANESE STYLE SC-59 PACKAGE



PACKAGING:

—	BULK, 500 per BAG
—	MAGAZINES OF 50 EACH
—	8mm T&R, T-146 3K/REEL
—	8mm T&R, T-147 3K/REEL
—	8mm T&R, T-246 10K/REEL
—	8mm T&R, T-247 10K/REEL

REMARKS: PROCESS: C-22 Thermal Resistance R_{θJA} 625 °C/Watt
FREE AIR, T_A = 25°C

ROHM ELECTRONICS 3034 Owen Drive, Antioch, TN 37013 TEL:(615)641-2020 FAX:(615)641-2022	APPROVAL	CHECK	DESIGN
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SUBJECT TRANSISTOR, NPN ,SILICON SOT-23	DATE January 14, 1987

ELECTRICAL CHARACTERISTICS: (Ta = 25°C Unless Otherwise Specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BVCBO	IC = 100 μA	60			V
BVCEO	IC = 10 mA	60			V
BVEBO	IE = 10 μA	6			V
ICBO	VCB = 60 V		2.0	100	nA
ICEO	VCE = 60 V		1.5	100	nA
IEBO	VEB = 6 V		1.0	100	nA
hFE	IC = 1.0 mA, VCE = 5.0 V	100		300	
hFE	IC = 10 mA, VCE = 5.0 V	100			
hFE	IC = 100 mA, VCE = 5.0 V	75			
VCE(SAT)	IC = 100 mA, IB = 5.0 mA			0.4	V
VCE(SAT)	IC = 100 mA, IB = 10 mA			0.3	V
VBE(ON)	IC = 1.0 mA, VCE = 5.0 V	0.5		0.7	V
fT	IC = 10 mA, VCE = 5.0 V, f = 100MHz	150	350		MHz
Cob	VCB = 5.0 V, IE = 0, f = 1.0 MHz			6.0	pF
Cib	VBE = 5.0 V, IC = 0, f = 1.0 MHz			25	pF

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